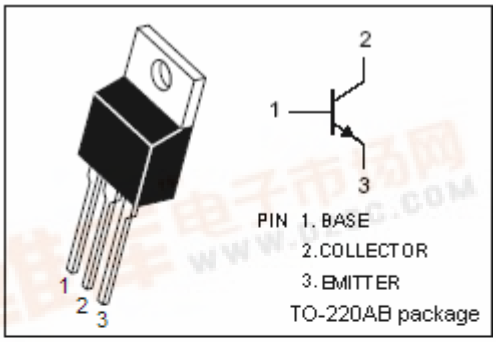
isc Silicon NPN Power Transistor 2SC2716



DESCRIPTION

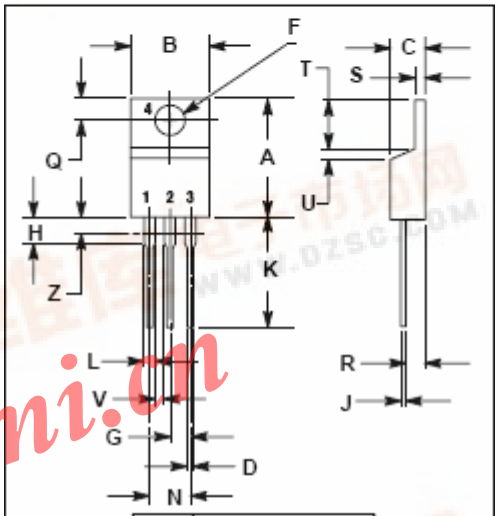
- High Power Gain-
  : $G_p \geqslant 12dB$,f= 27MHz, P_O= 16W
- High Reliability

APPLICATIONS

- Designed for RF power amplifier applications.

ABSOLUTE MAXIMUM RATINGS (T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5	V
I_{CM}	Collector Current	6	A
P_C	Collector Power Dissipation @T_C=25℃	20	W
	Collector Power Dissipation @T_a=25℃	1.7	
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	14.48	15.75
B	9.66	10.28
C	4.07	4.82
D	0.64	0.88
F	3.61	3.73
G	2.42	2.66
H	2.80	3.93
J	0.46	0.64
K	12.70	14.27
L	1.15	1.52
N	4.83	5.33
Q	2.54	3.04
R	2.04	2.79
S	1.15	1.39
T	5.97	6.47
U	0.00	1.27
V	1.15	---
Z	---	2.04

isc Silicon NPN Power Transistor 2SC2716

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 2A; I_B= 0.2A			1.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 30V; I_E= 0			0.1	mA
I_{CEO}	Collector Cutoff Current	V_{CE}= 25V; I_B= 0			0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 4V; I_C= 0			0.1	mA
h_{FE}	DC Current Gain	I_C= 0.5A; V_{CE}= 5V	20		180	
P_O	Output Power	V_{CC}= 12V;P_{in}= 1W, f=27MHz	16	18		W
η	Power Efficiency		60	70		%